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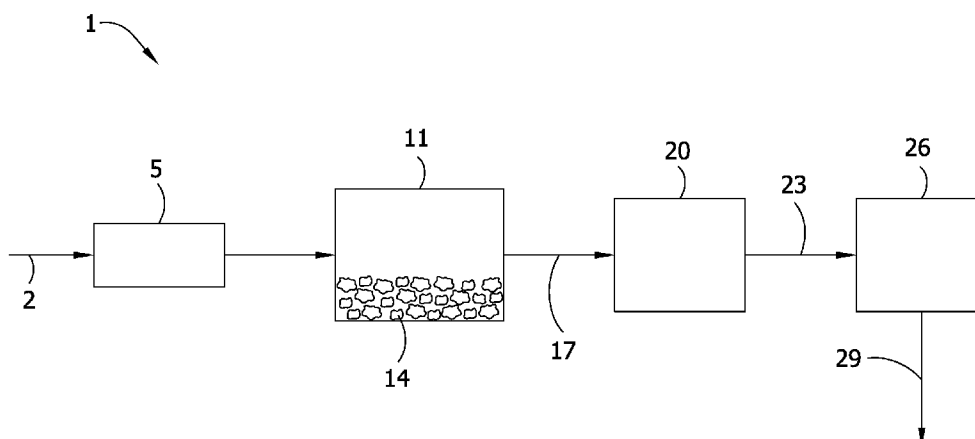
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(54) Title: METHOD FOR TREATMENT OF A GAS STREAM CONTAINING SILICON TETRAFLUORIDE AND HYDROGEN CHLORIDE

FIG. 1



(57) Abstract: The present invention is directed to a method for treatment of a gas stream comprising silicon tetrafluoride and hydrogen chloride. For example, the present invention is directed to a method for treatment of such a gas stream that involves contacting the gas stream with a metal that reacts with the hydrogen chloride to provide a treated gas stream having reduced hydrogen chloride content. The present invention is further directed to methods for subjecting silicon tetrafluoride and hydrogen chloride-containing gas streams to elevated pressure to provide gas streams suitable for transport.

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